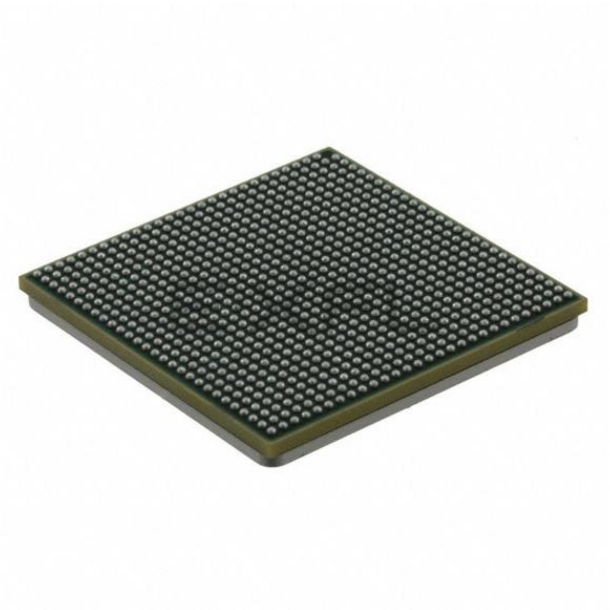

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8547hxaqg

— Performance monitor facility that is similar to, but separate from, the device performance monitor

The e500 defines features that are not implemented on this device. It also generally defines some features that this device implements more specifically. An understanding of these differences can be critical to ensure proper operations.

- 512-Kbyte L2 cache/SRAM
  - Flexible configuration.
  - Full ECC support on 64-bit boundary in both cache and SRAM modes
  - Cache mode supports instruction caching, data caching, or both.
  - External masters can force data to be allocated into the cache through programmed memory ranges or special transaction types (stashing).
  - 1, 2, or 4 ways can be configured for stashing only.
  - Eight-way set-associative cache organization (32-byte cache lines)
  - Supports locking entire cache or selected lines. Individual line locks are set and cleared through Book E instructions or by externally mastered transactions.
  - Global locking and Flash clearing done through writes to L2 configuration registers
  - Instruction and data locks can be Flash cleared separately.
  - SRAM features include the following:
    - I/O devices access SRAM regions by marking transactions as snoopable (global).
    - Regions can reside at any aligned location in the memory map.
    - Byte-accessible ECC is protected using read-modify-write transaction accesses for smaller-than-cache-line accesses.
- Address translation and mapping unit (ATMU)
  - Eight local access windows define mapping within local 36-bit address space.
  - Inbound and outbound ATMUs map to larger external address spaces.
    - Three inbound windows plus a configuration window on PCI/PCI-X and PCI Express
    - Four inbound windows plus a default window on RapidIO™
    - Four outbound windows plus default translation for PCI/PCI-X and PCI Express
    - Eight outbound windows plus default translation for RapidIO with segmentation and sub-segmentation support
- DDR/DDR2 memory controller
  - Programmable timing supporting DDR and DDR2 SDRAM
  - 64-bit data interface
  - Four banks of memory supported, each up to 4 Gbytes, to a maximum of 16 Gbytes
  - DRAM chip configurations from 64 Mbits to 4 Gbits with ×8/×16 data ports
  - Full ECC support
  - Page mode support
    - Up to 16 simultaneous open pages for DDR

- Single inbound doorbell message structure
- Facility to accept port-write messages

- PCI Express interface
  - PCI Express 1.0a compatible
  - Supports x8,x4,x2, and x1 link widths
  - Auto-detection of number of connected lanes
  - Selectable operation as root complex or endpoint
  - Both 32- and 64-bit addressing
  - 256-byte maximum payload size
  - Virtual channel 0 only
  - Traffic class 0 only
  - Full 64-bit decode with 32-bit wide windows
- Pin multiplexing for the high-speed I/O interfaces supports one of the following configurations:
  - 8 PCI Express
  - 4 PCI Express and 4 serial RapidIO
- Power management
  - Supports power saving modes: doze, nap, and sleep
  - Employs dynamic power management, which automatically minimizes power consumption of blocks when they are idle
- System performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter-specific events
  - Supports 64 reference events that can be counted on any of the eight counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- System access port
  - Uses JTAG interface and a TAP controller to access entire system memory map
  - Supports 32-bit accesses to configuration registers
  - Supports cache-line burst accesses to main memory
  - Supports large block (4-Kbyte) uploads and downloads
  - Supports continuous bit streaming of entire block for fast upload and download
- JTAG boundary scan, designed to comply with IEEE Std. 1149.1™

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the device. The following table provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Table 8. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	µs	—
Minimum assertion time for $\overline{\text{SRESET}}$	3	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	µs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Note:

1. SYSCLK is the primary clock input for the device.

The following table provides the PLL lock times.

Table 9. PLL Lock Times

Parameter/Condition	Min	Max	Unit
Core and platform PLL lock times	—	100	µs
Local bus PLL lock time	—	50	µs
PCI/PCI-X bus PLL lock time	—	50	µs

5.1 Power-On Ramp Rate

This section describes the AC electrical specifications for the power-on ramp rate requirements. Controlling the maximum power-on ramp rate is required to avoid falsely triggering the ESD circuitry. The following table provides the power supply ramp rate specifications.

Table 10. Power Supply Ramp Rate

Parameter	Min	Max	Unit	Notes
Required ramp rate for MVREF	—	3500	V/s	1
Required ramp rate for VDD	—	4000	V/s	1, 2

Note:

1. Maximum ramp rate from 200 to 500 mV is most critical as this range may falsely trigger the ESD circuitry.
2. VDD itself is not vulnerable to false ESD triggering; however, as per Section 22.2, “PLL Power Supply Filtering,” the recommended AVDD_CORE, AVDD_PLAT, AVDD_LBIU, AVDD_PCI1 and AVDD_PCI2 filters are all connected to VDD. Their ramp rates must be equal to or less than the VDD ramp rate.

Table 13 provides the recommended operating conditions for the DDR SDRAM controller when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.15$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.15$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 \text{ V} \le V_{OUT} \le GV_{DD}$.

Table 14 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 14. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 19. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MCK[n] cycle time, MCK[*n*]/$\overline{\text{MCK}}$[*n*] crossing	t_{MCK}	3.75	6	ns	2
ADDR/CMD output setup with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHAS}	 1.48 1.95 2.40	 — — —	ns	3
ADDR/CMD output hold with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHAX}	 1.48 1.95 2.40	 — — —	ns	3
$\overline{\text{MCS}}$[*n*] output setup with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHCS}	 1.48 1.95 2.40	 — — —	ns	3
$\overline{\text{MCS}}$[*n*] output hold with respect to MCK 533 MHz 400 MHz 333 MHz	t_{DDKHCX}	 1.48 1.95 2.40	 — — —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS 533 MHz 400 MHz 333 MHz	t_{DDKHDS}, t_{DDKLDS}	 538 700 900	 — — —	ps	5
MDQ/MECC/MDM output hold with respect to MDQS 533 MHz 400 MHz 333 MHz	t_{DDKHDX}, t_{DDKLDX}	 538 700 900	 — — —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the device.

7.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface.

Table 20. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}[1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

7.2 DUART AC Electrical Specifications

This table provides the AC timing parameters for the DUART interface.

Table 21. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	f_{CCB}/1,048,576	baud	1, 2
Maximum baud rate	f_{CCB}/16	baud	1, 2, 3
Oversample rate	16	—	1, 4

Notes:
1. Guaranteed by design.
2. f_{CCB} refers to the internal platform clock.
3. Actual attainable baud rate is limited by the latency of interrupt processing.
4. The middle of a start bit is detected as the 8^{th} sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16^{th} sample.

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the device.

10.1 Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 3.3 V DC.

Table 38. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}[1] = 0 V or V_{IN} = BV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (BV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 39 provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 2.5 V DC.

Table 39. Local Bus DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	1.70	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.7	V
Input current (V_{IN}[1] = 0 V or V_{IN} = BV_{DD})	I_{IH}	—	10	μA
	I_{IL}		–15	
High-level output voltage (BV_{DD} = min, I_{OH} = –1 mA)	V_{OH}	2.0	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 1 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

10.2 Local Bus AC Electrical Specifications

This table describes the timing parameters of the local bus interface at BV_{DD} = 3.3 V. For information about the frequency range of local bus, see Section 20.1, “Clock Ranges.”

Table 40. Local Bus Timing Parameters (BV_{DD} = 3.3 V)—PLL Enabled

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{LGTA}$/LUPWAIT)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
$\overline{LGTA}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except $\overline{LGTA}$/LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
$\overline{LGTA}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.2	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.7	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[*n*]. Skew measured between complementary signals at $BV_{DD}/2$.
8. Guaranteed by design.

Figure 31 provides the $\overline{\text{TRST}}$ timing diagram.

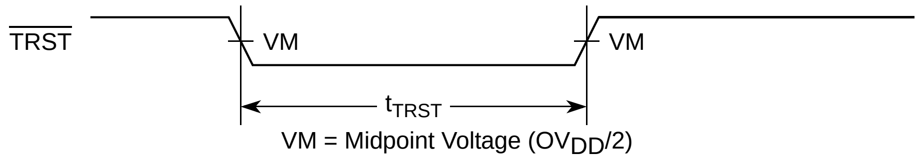

Figure 31. $\overline{\text{TRST}}$ Timing Diagram

Figure 32 provides the boundary-scan timing diagram.

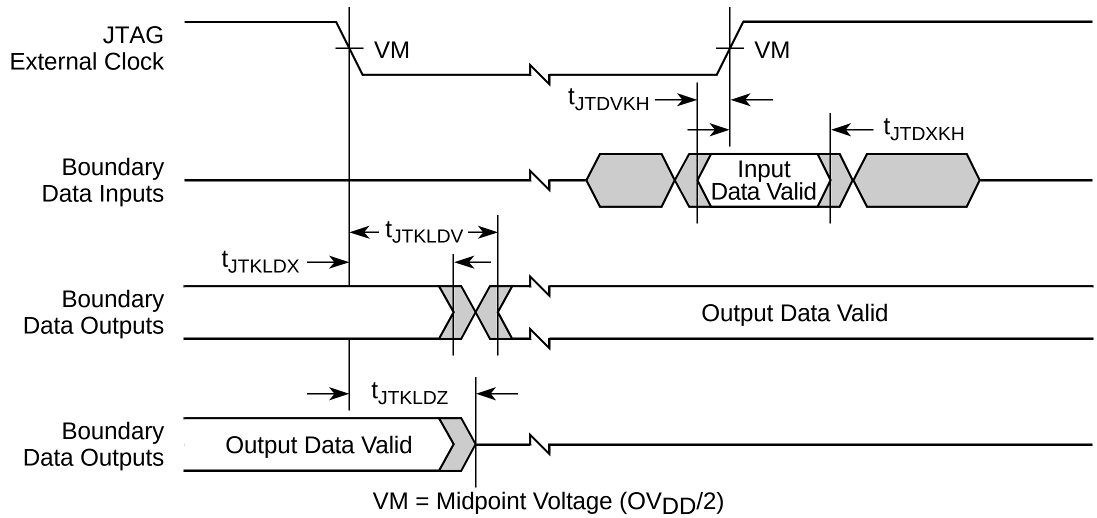

Figure 32. Boundary-Scan Timing Diagram

Figure 34 shows the AC timing diagram for the I²C bus.

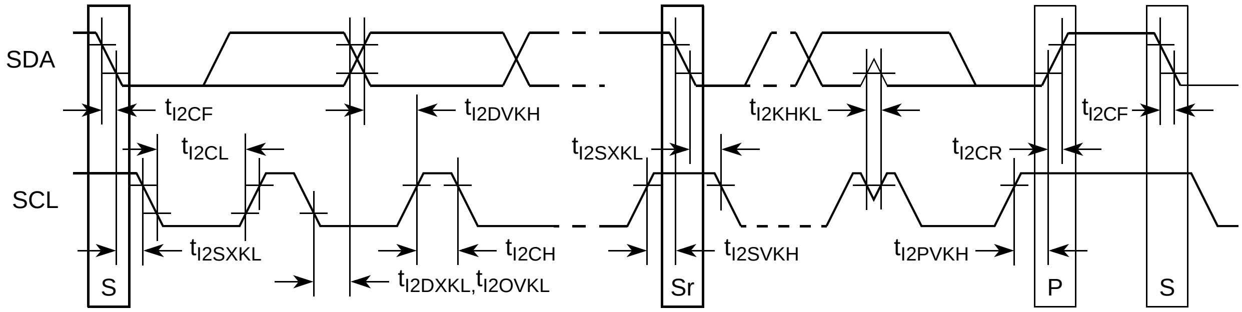

Figure 34. I²C Bus AC Timing Diagram

16 High-Speed Serial Interfaces (HSSI)

The device features one Serializer/Deserializer (SerDes) interface to be used for high-speed serial interconnect applications. The SerDes interface can be used for PCI Express and/or serial RapidIO data transfers.

This section describes the common portion of SerDes DC electrical specifications, which is the DC requirement for SerDes reference clocks. The SerDes data lane's transmitter and receiver reference circuits are also shown.

16.1 Signal Terms Definition

The SerDes utilizes differential signaling to transfer data across the serial link. This section defines terms used in the description and specification of differential signals.

Figure 38 shows how the signals are defined. For illustration purpose, only one SerDes lane is used for the description. The figure shows a waveform for either a transmitter output (SD_TX and $\overline{\text{SD\_TX}}$) or a receiver input (SD_RX and $\overline{\text{SD\_RX}}$). Each signal swings between A volts and B volts where A > B.

Using this waveform, the definitions are as follows. To simplify the illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

- Single-ended swing
  The transmitter output signals and the receiver input signals SD_TX, $\overline{\text{SD\_TX}}$, SD_RX and $\overline{\text{SD\_RX}}$ each have a peak-to-peak swing of A – B volts. This is also referred as each signal wire's single-ended swing.
- Differential output voltage, V_{OD} (or differential output swing):
  The differential output voltage (or swing) of the transmitter, V_{OD}, is defined as the difference of the two complimentary output voltages: $V_{SD\_TX} - V_{\overline{SD\_TX}}$. The V_{OD} value can be either positive or negative.
- Differential input voltage, V_{ID} (or differential input swing):
  The differential input voltage (or swing) of the receiver, V_{ID}, is defined as the difference of the two complimentary input voltages: $V_{SD\_RX} - V_{\overline{SD\_RX}}$. The V_{ID} value can be either positive or negative.
- Differential peak voltage, V_{DIFFp}
  The peak value of the differential transmitter output signal or the differential receiver input signal is defined as differential peak voltage, $V_{DIFFp} = |A - B|$ volts.
- Differential peak-to-peak, $V_{DIFFp\text{-}p}$
  Because the differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as differential peak-to-peak voltage, $V_{DIFFp\text{-}p} = 2 \times V_{DIFFp} = 2 \times |(A - B)|$ volts, which is twice of differential swing in amplitude, or twice of the differential peak. For example, the output differential peak-to-peak voltage can also be calculated as $V_{TX\text{-}DIFFp\text{-}p} = 2 \times |V_{OD}|$.
- Common mode voltage, V_{cm}
  The common mode voltage is equal to one half of the sum of the voltages between each conductor

17 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus of the MPC8548E.

17.1 DC Requirements for PCI Express SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$

For more information, see Section 16.2, "SerDes Reference Clocks."

17.2 AC Requirements for PCI Express SerDes Clocks

Table 55 lists the AC requirements for the PCI Express SerDes clocks.

Table 55. SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ AC Requirements

Symbol	Parameter Description	Min	Typ	Max	Unit	Notes
t_{REF}	REFCLK cycle time	—	10	—	ns	1
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles.	—	—	100	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location.	–50	—	50	ps	—

Note:
1. Typical based on *PCI Express Specification 2.0*.

17.3 Clocking Dependencies

The ports on the two ends of a link must transmit data at a rate that is within 600 parts per million (ppm) of each other at all times. This is specified to allow bit rate clock sources with a ±300 ppm tolerance.

17.4 Physical Layer Specifications

The following is a summary of the specifications for the physical layer of PCI Express on this device. For further details as well as the specifications of the transport and data link layer see *PCI Express Base Specification. Rev. 1.0a*.

17.4.1 Differential Transmitter (TX) Output

Table 56 defines the specifications for the differential output at all transmitters (TXs). The parameters are specified at the component pins.

Table 56. Differential Transmitter (TX) Output Specifications (continued)

Symbol	Parameter	Min	Nom	Max	Unit	Comments
$V_{TX\text{-}DC\text{-}CM}$	The TX DC common mode voltage	0	—	3.6	V	The allowed DC common mode voltage under any conditions. See Note 6.
$I_{TX\text{-}SHORT}$	TX short circuit current limit	—	—	90	mA	The total current the transmitter can provide when shorted to its ground
$T_{TX\text{-}IDLE\text{-}MIN}$	Minimum time spent in electrical idle	50	—		UI	Minimum time a transmitter must be in electrical idle utilized by the receiver to start looking for an electrical idle exit after successfully receiving an electrical idle ordered set
$T_{TX\text{-}IDLE\text{-}SET\text{-}TO\text{-}IDLE}$	Maximum time to transition to a valid electrical idle after sending an electrical idle ordered set	—	—	20	UI	After sending an electrical idle ordered set, the transmitter must meet all electrical idle specifications within this time. This is considered a debounce time for the transmitter to meet electrical idle after transitioning from L0.
$T_{TX\text{-}IDLE\text{-}TO\text{-}DIFF\text{-}DATA}$	Maximum time to transition to valid TX specifications after leaving an electrical idle condition	—	—	20	UI	Maximum time to meet all TX specifications when transitioning from electrical idle to sending differential data. This is considered a debounce time for the TX to meet all TX specifications after leaving electrical idle
$RL_{TX\text{-}DIFF}$	Differential return loss	12	—	—	dB	Measured over 50 MHz to 1.25 GHz. See Note 4.
$RL_{TX\text{-}CM}$	Common mode return loss	6	—	—	dB	Measured over 50 MHz to 1.25 GHz. See Note 4.
$Z_{TX\text{-}DIFF\text{-}DC}$	DC differential TX impedance	80	100	120	Ω	TX DC differential mode low impedance
$Z_{TX\text{-}DC}$	Transmitter DC impedance	40	—	—	Ω	Required TX D+ as well as D– DC impedance during all states
$L_{TX\text{-}SKEW}$	Lane-to-lane output skew	—	—	500 + 2 UI	ps	Static skew between any two transmitter lanes within a single Link
C_{TX}	AC coupling capacitor	75	—	200	nF	All transmitters shall be AC coupled. The AC coupling is required either within the media or within the transmitting component itself. See note 8.

19 Package Description

This section details package parameters, pin assignments, and dimensions.

19.1 Package Parameters

The package parameters for both the HiCTE FC-CBGA and FC-PBGA are provided in Table 70.

Table 70. Package Parameters

Parameter	CBGA[1]	PBGA[2]
Package outline	29 mm × 29 mm	29 mm × 29 mm
Interconnects	783	783
Ball pitch	1 mm	1 mm
Ball diameter (typical)	0.6 mm	0.6 mm
Solder ball	63% Sn 37% Pb 0% Ag	63% Sn 37% Pb 0% Ag
Solder ball (lead-free)	95% Sn 4.5% Ag 0.5% Cu	96.5% Sn 3.5% Ag

Notes:
1. The HiCTE FC-CBGA package is available on only Version 2.0 of the device.
2. The FC-PBGA package is available on only versions 2.1.1 and 2.1.2, and 3.0 of the device.

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core Power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad Power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
IRQ[0:7]	AG23, AF18, AE18, AF20, AG18, AF17, AH24, AE20	I	OV_{DD}	—
IRQ[8]	AF19	I	OV_{DD}	—
IRQ[9]/$\overline{\text{DMA\_DREQ3}}$	AF21	I	OV_{DD}	1
IRQ[10]/$\overline{\text{DMA\_DACK3}}$	AE19	I/O	OV_{DD}	1
IRQ[11]/$\overline{\text{DMA\_DDONE3}}$	AD20	I/O	OV_{DD}	1
$\overline{\text{IRQ\_OUT}}$	AD18	O	OV_{DD}	2, 4
Ethernet Management Interface				
EC_MDC	AB9	O	OV_{DD}	5, 9
EC_MDIO	AC8	I/O	OV_{DD}	—
Gigabit Reference Clock				
EC_GTX_CLK125	V11	I	LV_{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_RXD[7:0]	R5, U1, R3, U2, V3, V1, T3, T2	I	LV_{DD}	—
TSEC1_TXD[7:0]	T10, V7, U10, U5, U4, V6, T5, T8	O	LV_{DD}	5, 9
TSEC1_COL	R4	I	LV_{DD}	—
TSEC1_CRS	V5	I/O	LV_{DD}	20
TSEC1_GTX_CLK	U7	O	LV_{DD}	—
TSEC1_RX_CLK	U3	I	LV_{DD}	—
TSEC1_RX_DV	V2	I	LV_{DD}	—
TSEC1_RX_ER	T1	I	LV_{DD}	—
TSEC1_TX_CLK	T6	I	LV_{DD}	—
TSEC1_TX_EN	U9	O	LV_{DD}	30
TSEC1_TX_ER	T7	O	LV_{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 2)				
TSEC2_RXD[7:0]	P2, R2, N1, N2, P3, M2, M1, N3	I	LV_{DD}	—
TSEC2_TXD[7:0]	N9, N10, P8, N7, R9, N5, R8, N6	O	LV_{DD}	5, 9, 33
TSEC2_COL	P1	I	LV_{DD}	—
TSEC2_CRS	R6	I/O	LV_{DD}	20
TSEC2_GTX_CLK	P6	O	LV_{DD}	—
TSEC2_RX_CLK	N4	I	LV_{DD}	—
TSEC2_RX_DV	P5	I	LV_{DD}	—
TSEC2_RX_ER	R1	I	LV_{DD}	—
TSEC2_TX_CLK	P10	I	LV_{DD}	—
TSEC2_TX_EN	P7	O	LV_{DD}	30

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DFT				
L1_TSTCLK	AC25	I	OV_{DD}	25
L2_TSTCLK	AE22	I	OV_{DD}	25
$\overline{\text{LSSD\_MODE}}$	AH20	I	OV_{DD}	25
$\overline{\text{TEST\_SEL}}$	AH14	I	OV_{DD}	25
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV_{DD}	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV_{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV_{DD}	—
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5 V)	GV_{DD}	—

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MDIC[0:1]	A19, B19	I/O	GV_{DD}	36
Local Bus Controller Interface				
LAD[0:31]	E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21	I/O	BV_{DD}	—
LDP[0:3]	K21, C28, B26, B22	I/O	BV_{DD}	—
LA[27]	H21	O	BV_{DD}	5, 9
LA[28:31]	H20, A27, D26, A28	O	BV_{DD}	5, 7, 9
$\overline{\text{LCS}}$[0:4]	J25, C20, J24, G26, A26	O	BV_{DD}	—
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	D23	I/O	BV_{DD}	1
$\overline{\text{LCS6}}$/$\overline{\text{DMA\_DACK2}}$	G20	O	BV_{DD}	1
$\overline{\text{LCS7}}$/$\overline{\text{DMA\_DDONE2}}$	E21	O	BV_{DD}	1
$\overline{\text{LWE0}}$/$\overline{\text{LBS0}}$/LSDDQM[0]	G25	O	BV_{DD}	5, 9
$\overline{\text{LWE1}}$/$\overline{\text{LBS1}}$/LSDDQM[1]	C23	O	BV_{DD}	5, 9
$\overline{\text{LWE2}}$/$\overline{\text{LBS2}}$/LSDDQM[2]	J21	O	BV_{DD}	5, 9
$\overline{\text{LWE3}}$/$\overline{\text{LBS3}}$/LSDDQM[3]	A24	O	BV_{DD}	5, 9
LALE	H24	O	BV_{DD}	5, 8, 9
LBCTL	G27	O	BV_{DD}	5, 8, 9
LGPL0/LSDA10	F23	O	BV_{DD}	5, 9
LGPL1/$\overline{\text{LSDWE}}$	G22	O	BV_{DD}	5, 9
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LSDRAS}}$	B27	O	BV_{DD}	5, 8, 9
LGPL3/$\overline{\text{LSDCAS}}$	F24	O	BV_{DD}	5, 9
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/LPBSE	H23	I/O	BV_{DD}	—
LGPL5	E26	O	BV_{DD}	5, 9
LCKE	E24	O	BV_{DD}	—
LCLK[0:2]	E23, D24, H22	O	BV_{DD}	—
LSYNC_IN	F27	I	BV_{DD}	—
LSYNC_OUT	F28	O	BV_{DD}	—
DMA				
$\overline{\text{DMA\_DACK}}$[0:1]	AD3, AE1	O	OV_{DD}	5, 9, 106
$\overline{\text{DMA\_DREQ}}$[0:1]	AD4, AE2	I	OV_{DD}	—
$\overline{\text{DMA\_DDONE}}$[0:1]	AD2, AD1	O	OV_{DD}	—
Programmable Interrupt Controller				

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{PCI1\_TRDY}}$	AG11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_REQ}}$[4:1]	AH2, AG4, AG3, AH4	I	OV_{DD}	—
$\overline{\text{PCI1\_REQ0}}$	AH3	I/O	OV_{DD}	—
PCI1_CLK	AH26	I	OV_{DD}	39
$\overline{\text{PCI1\_DEVSEL}}$	AH11	I/O	OV_{DD}	2
$\overline{\text{PCI1\_FRAME}}$	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
cfg_pci1_width	AF14	I/O	OV_{DD}	112
Reserved	V15	—	—	110
Reserved	AE28	—	—	2
Reserved	AD26	—	—	110
Reserved	AD25	—	—	110
Reserved	AE26	—	—	110
cfg_pci1_clk	AG24	I	OV_{DD}	5
Reserved	AF25	—	—	101
Reserved	AE25	—	—	110
Reserved	AG25	—	—	110
Reserved	AD24	—	—	110
Reserved	AF24	—	—	110
Reserved	AD27	—	—	110
Reserved	AD28, AE27, W17, AF26	—	—	110
Reserved	AH25	—	—	110
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
$\overline{\text{MDQS}}$[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—

- First, the board must have at least 10 × 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors must be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors must be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there must be a 1-µF ceramic chip capacitor from each SerDes supply (SV_{DD} and XV_{DD}) to the board ground plane on each side of the device. This must be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there must be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This must be done for all SerDes supplies.

22.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. All unused active low inputs must be tied to V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD}, as required. All unused active high inputs must be connected to GND. All NC (no-connect) signals must remain unconnected. Power and ground connections must be made to all external V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND pins of the device.

22.6 Pull-Up and Pull-Down Resistor Requirements

The device requires weak pull-up resistors (2–10 kΩ is recommended) on open drain type pins including I^2C pins and PIC (interrupt) pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 63. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion gives unpredictable results.

The following pins must not be pulled down during power-on reset: TSEC3_TXD[3], $\overline{\text{HRESET\_REQ}}$, TRIG_OUT/READY/$\overline{\text{QUIESCE}}$, MSRCID[2:4], ASLEEP. The $\overline{\text{DMA\_DACK}}$[0:1], and TEST_SEL/ TEST_SEL pins must be set to a proper state during POR configuration. See the pinlist table of the individual device for more details

See the PCI 2.2 specification for all pull ups required for PCI.

22.7 Output Buffer DC Impedance

The device drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 61). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.